SCAS299A - JANUARY 1993 - REVISED JULY 1995

- EPIC ™ (Enhanced-Performance Implanted **CMOS) Submicron Process**
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) **Packages**

(TOP VIEW)

DB. DW. OR PW PACKAGE

LEBA [_	24	J ∨cc
OEBA [2		23	CEBA
A1 [3		22	B1
A2 [4		21	B2
A3 [5		20] B3
A4 [6		19] B4
A5 [7		18] B5
A6 [8		17] B6
A7 [9		16] B7
A8 [10		15] B8
CEAB [11		14	LEAB
GND [12		13	OEAB

description

This octal registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC543 contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{\text{LEAB}}$ or $\overline{\text{LEBA}}$) and output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable (CEAB) input must be low to enter data from A or to output data from B. If CEAB is low and LEAB is low, the A-to-B latches are transparent; a subsequent low-to-high transition of LEAB places the A latches in the storage mode. With $\overline{\mathsf{CEAB}}$ and $\overline{\mathsf{OEAB}}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow for B to A is similar to that of A to B but uses $\overline{\mathsf{CEBA}}$, $\overline{\mathsf{LEBA}}$, and $\overline{\mathsf{OEBA}}$.

To ensure the high-impedance state during power up or power down, $\overline{\sf OE}$ should be tied to ${\sf V}_{\sf CC}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC543 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE[†]

	INPUTS					
CEAB	LEAB	OEAB	Α	В		
Н	Х	Х	Х	Z		
Х	Χ	Н	Χ	Z		
L	Н	L	Χ	в ₀ ‡		
L	L	L	L	L		
L	L	L	Н	н		

[†] A-to-B data flow is shown; B-to-A flow control is the same except that it uses CEBA, LEBA, and OEBA.



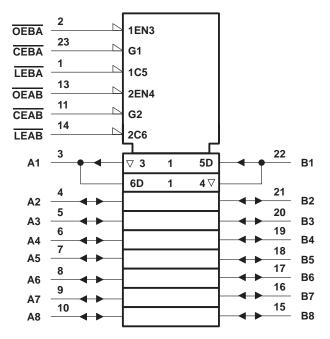
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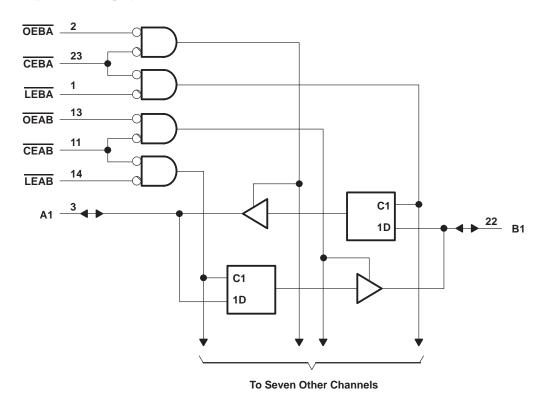
[‡] Output level before the indicated steady-state input conditions were established

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





SCAS299A - JANUARY 1993 - REVISED JULY 1995

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	0.5 V to 4.6 V
Input voltage range, V _I : Except I/O ports (see Note 1)	0.5 V to 6.5 V
I/O ports (see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Output voltage range, VO (see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, $I_{ K }(V_{ C } < 0)$	–50 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Maximum power dissipation at T _A = 55°C (in still air) (see Note 3): DB package	ge 0.65 W
DW packag	ge 1.7 W
PW packag	ge 0.7 W
Storage temperature range, T _{stq}	65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 4.6 V maximum.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
Vcc	Supply voltage		2.7	3.6	V
VIH	High-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
VIL	Low-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	V
\/.	Input voltage	Control inputs	0	5.5	V
VI	input voitage	Data inputs	0	VCC	V
Vo	Output voltage		0	VCC	V
la	$V_{CC} = 2.7 \text{ V}$	V _{CC} = 2.7 V		-12	mA
IОН	High-level output current	V _{CC} = 3 V		-24	IIIA
la.	Low-level output current	V _{CC} = 2.7 V		12	mA
IOL	V _{CC} = 3 V			24	IIIA
Δt/Δν	Input transition rise or fall rate		0	10	ns/V
TA	Operating free-air temperature		-40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.



^{3.} The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

SN74LVC543 OCTAL REGISTERED TRANSCEIVER WITH 3-STATE OUTPUTS

SCAS299A - JANUARY 1993 - REVISED JULY 1995

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST C	ONDITIONS	v _{CC} †	MIN	TYP‡	MAX	UNIT
		I _{OH} = -100 μA		MIN to MAX	V _{CC} −0.2	2		
\/-··		I _{OH} = - 12 mA		2.7 V	2.2			v
VOH				3 V	2.4			V
				3 V	2.2			
		I _{OL} = 100 μA		MIN to MAX			0.2	
VOL		$I_{OL} = 12 \text{ mA}$		2.7 V			0.4	V
		I _{OL} = 24 mA		3 V			0.55	
II		V _I = 5.5 V or GND		3.6 V			±5	μΑ
loz§		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ
Icc		$V_I = V_{CC}$ or GND,	I _O = 0	3.6 V			20	μΑ
Δlcc	_	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			500	μΑ
Ci	Control inputs	V _I = V _{CC} or GND		3.3 V		4.6		pF
C _{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7.2		pF

[†] For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t _W	Pulse duration	4		4		ns
t _{su}	Setup time, data before LE↑ or CE↑	1.5		1.5		ns
th	Hold time, data after LE↑ or CE↑	2.5		2.5		ns

switching characteristics over recommended operating free-air temperature range, C_I = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		UNIT
	(INFOT)	(INPUT) (OUTPUT)	MIN	MAX	MIN	MAX	
	A or B	1.5	8		9	no	
^t pd	LE	B or A	1.5	9.5		10.5	ns
	OE A SER	1.5	8.5		9.5		
t _{en}	CE	A or B	1.5	9		10	ns
^t dis	ŌĒ	4 5	1.5	8.5		9.5	
	CE	A or B	1.5	9		10	ns

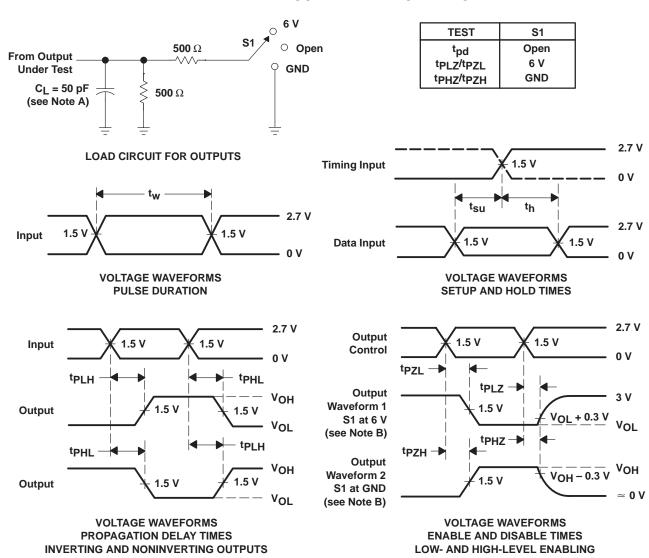


 $[\]ddagger$ All typical values are at VCC = 3.3 V, TA = 25°C. § For I/O ports, the parameter IOZ includes the input leakage current.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER			TEST COI	TYP	UNIT
C _{pd} Power dissipation capacitance per transceiver	Outputs enabled	C 50 pF	C: F0 =		n.E
	Outputs disabled	$C_L = 50 \text{ pF},$	f = 10 MHz	4.6	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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